P-Channel Enhancement Mode MOSFET

Description

The IPD85P04P4L06ATMA2 uses advanced trench technology to provide excellent RDS(ON), low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

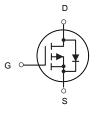


TO-252-2L

General Features

 $V_{DS} = -40V I_{D} = -80A$

 $R_{DS(ON)}$ < 8.2 m Ω @ V_{GS} =10V



Application

Battery protection

Load switch

Uninterruptible power supply

P-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
IPD85P04P4L06ATMA2	TO-252-2L	HXY MOSFET	2500

Absolute Maximum Ratings (T_c=25°Cunless otherwise noted)

Symbol	Parameter	Rating	Units
VDS	Drain-Source Voltage	-40	V
VGS	Gate-Source Voltage	urce Voltage ±20	
I _D @T _C =25°C	Continuous Drain Current, V _{GS} @ 10V ¹	Drain Current, V _{GS} @ 10V ¹ -80	
I _D @T _C =100°C	Continuous Drain Current, V _{GS} @ 10V ¹	Drain Current, V _{GS} @ 10V ¹ -50	
IDM	Pulsed Drain Current ²	Pulsed Drain Current ² -320	
P _D @T _C =25°C	Total Power Dissipation ⁴	81	W
TSTG	Storage Temperature Range	-55 to 150	°C
TJ	Operating Junction Temperature Range	-55 to 150	°C
ReJA	Thermal Resistance Junction-ambient ¹	mal Resistance Junction-ambient ¹ 54	
R₀JC	Thermal Resistance Junction-Case ¹	1.54	°C/W



Electrical Characteristics (T_J=25°C,unless otherwise noted)

Parameter		Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static Characteristics			,		1	1		
Drain-Source Breakdown Volta	Drain-Source Breakdown Voltage		V _G S = 0V, I _D = -250µA	-40	_	_	V	
Gate-body Leakage current		Igss	V _{DS} = 0V, V _{GS} = ±20V	_	_	±100	nA	
Zero Gate Voltage Drain Current	T _J =25°C			-	-	-1	- pA	
	T _J =100°C	- IDSS	V _{DS} = -40V, V _{GS} = 0V	-	-	-100		
Gate-Threshold Voltage		V _G S(th)	V _{DS} = V _{GS} , I _D = -250μA	-1.0	-1.6	-2.5	V	
		_	V _G S = -10V, I _D = -20A	-	6.4	8.2		
Drain-Source on-Resistance ⁴		RDS(on)	V _G S = -4.5V, I _D = -15A	-	8.2	11	⊢ mQ	
Forward Transconductance4		G fs	V _{DS} = -10V, I _D = -20A	-	104	-	S	
Dynamic Characteristics ⁵				-	1			
Input Capacitance		Ciss		_	5295	_		
Output Capacitance Reverse Transfer Capacitance		Coss	V _{DS} = -20V, V _{GS} =0V, f =1MHz	-	430	-	pF	
		Crss		_	385	_		
Gate Resistance		Rg	f =1MHz	_	4.3	_	Q	
Switching Characteristics	5	-						
Total Gate Charge		Qg		_	110	_		
Gate-Source Charge		Qgs	Vgs = -10V, Vps = -20V,	-	12.5	_	nC	
Gate-Drain Charge	Gate-Drain Charge		- ID20A	-	23	_		
Turn-on Delay Time		td(on)		-	16.8	-		
Rise Time		t _r	V _{GS} = -10V, V _{DD} = -20V,	-	10	-	ns	
Turn-off Delay Time		t _{d(off)}	$R_G = 3\Omega$, $I_D = -20A$	-	65	-	113	
Fall Time		tf		_	17	-		
Body Diode Reverse Recovery Time		t _{rr}		_	42	_	ns	
Body Diode Reverse Recovery Charge		Q _{rr}	- I _F = -20A, dl/dt= 100A/μs	_	29	_	nC	
Drain-Source Body Diode	Characteris	tics	1	1	1	1		
Diode Forward Voltage ⁴		Vsp	I _S = -20A, V _{GS} = 0V	_	_	-1.2	V	
Continuous Source Current	Tc=25°C	Is	_	<u> </u>	_	-80	Α	

Notes:

- 1. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150°C.
- 2. The EAS data shows Max. rating . The test condition is V_{DD} = -30V, V_{GS} = -10V, L= 0.1mH, I_{AS}= -45A.
- 3. The data tested by surface mounted on a 1 inch2 FR-4 board with 2OZ copper, The value in any given application depends on the user's specific board design.
- 4. The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%.
- 5. This value is guaranteed by design hence it is not included in the production test.



Typical Characteristics

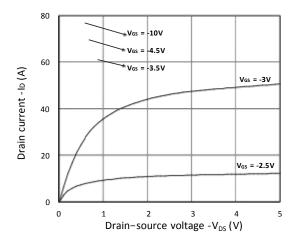


Figure 1. Output Characteristics

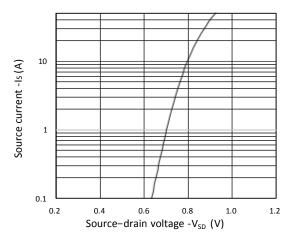


Figure 3. Forward Characteristics of Reverse

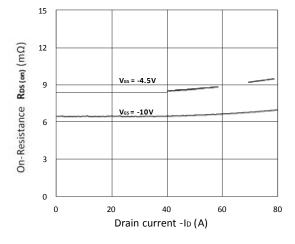


Figure 5. $R_{DS(ON)} \, vs$. I_D

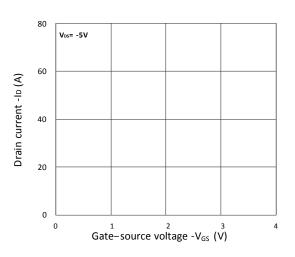


Figure 2. Transfer Characteristics

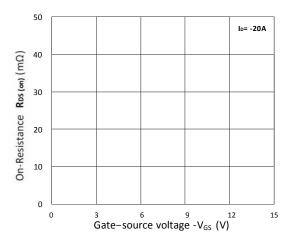


Figure 4. $R_{\text{DS}(\text{ON})} \ vs$. V_{GS}

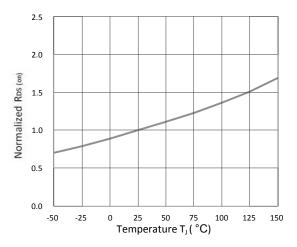
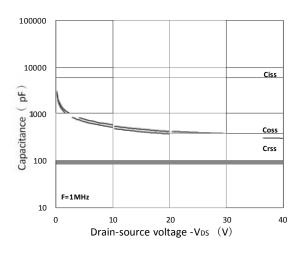
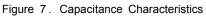


Figure 6. Normalized $R_{\text{DS}(\text{on})} \ \text{vs}$. Temperature





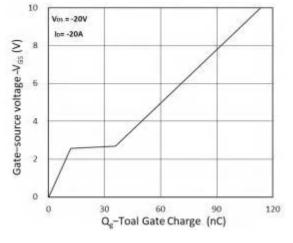


Figure 8. Gate Charge Characteristics

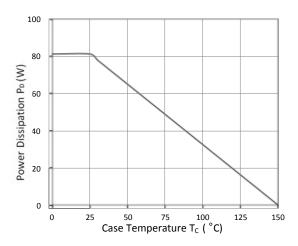


Figure 9. Power Dissipation

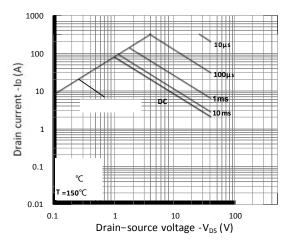


Figure 10. Safe Operating Area

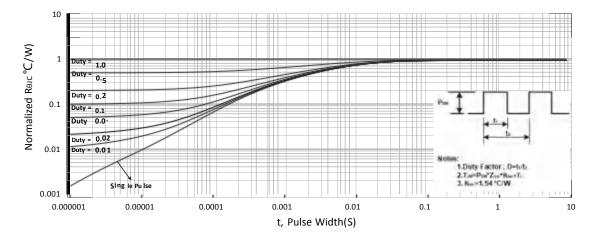
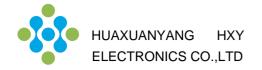


Figure 11. Normalized Maximum Transient Thermal Impedance



Test Circuit

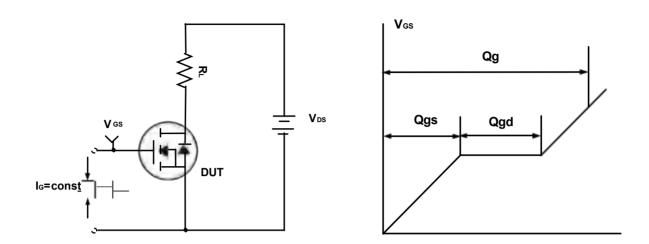


Figure A. Gate Charge Test Circuit & Waveforms

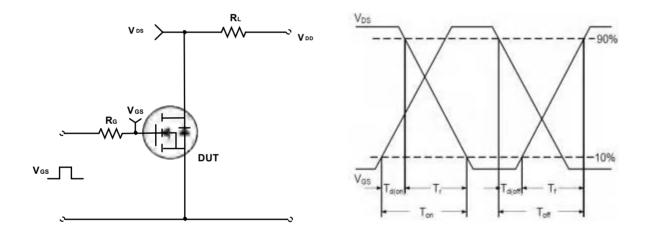


Figure B. Switching Test Circuit & Waveforms

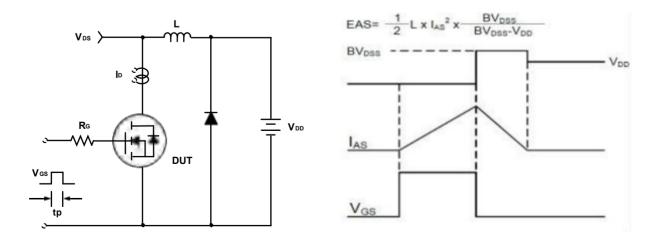
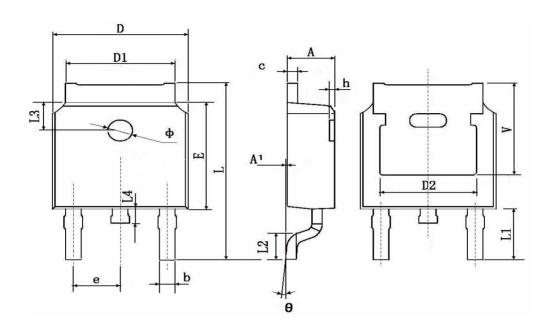


Figure C. Unclamped Inductive Switching Circuit & Waveforms



TO-252-2L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches			
	Min.	Max.	Min.	Max.		
А	2.200	2.400	0.087	0.094		
A1	0.000	0.127	0.000	0.005		
b	0.660	0.860	0.026	0.034		
С	0.460	0.580	0.018	0.023		
D	6.500	6.700	0.256	0.264		
D1	5.100	5.460	0.201	0.215		
D2	4.830 TYP.		0.190 TYP.			
E	6.000	6.200	0.236	0.244		
е	2.186	2.386	0.086	0.094		
L	9.800	10.400	0.386	0.409		
L1	2.900 TYP.		0.114 TYP.			
L2	1.400	1.700	0.055	0.067		
L3	1.600	1.600 TYP.		0.063 TYP.		
L4	0.600	1.000	0.024	0.039		
Ф	1.100	1.300	0.043	0.051		
θ	0°	8°	0°	8°		
h	0.000	0.300	0.000	0.012		
V	5.350 TYP.		0.211 TYP.			

IPD85P04P4L06ATMA2

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